



Pin	Symbol		Function
1	GND	-	Logic ground
2	IN	I	Input, activates the power switch in case of logical high signal
3	Vbb	+	Positive power supply voltage, the tab is shorted to this pin
4	ST	S	Diagnostic feedback, low on failure
5	OUT (Load, L)	0	Output to the load



Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	$V_{ m bb}$	43	V
Supply voltage for short circuit protection $T_{\rm jStart}$ =-40+150°C	V _{bb}	34	V
Load dump protection ²⁾ $V_{\text{LoadDump}} = U_{\text{A}} + V_{\text{S}}, U_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}}^{3)} = 2 \Omega, R_{\text{L}} = 5.3 \Omega, t_{\text{d}} = 200 \text{ ms}, \text{IN} = \text{low or high}$	V _{Load dump} ⁴⁾	60	V
Load current (Short circuit current, see page 5)	<i>I</i> L	self-limited	Α
Operating temperature range	T _j	-40+150	°C
Storage temperature range	$T_{ m stg}$	-55+150	
Power dissipation (DC), T _C ≤ 25 °C	P _{tot}	18	W
Inductive load switch-off energy dissipation, single pulse $V_{bb} = 12V$, $T_{j,start} = 150$ °C, $T_{C} = 150$ °C const. $I_{L} = 2.3 \text{ A}$, $Z_{L} = 98 \text{ mH}$, 0 Ω :	E _{AS}	335	mJ
Electrostatic discharge capability (ESD) IN: (Human Body Model) all other pins: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993	V _{ESD}	1.0 2.0	kV
Input voltage (DC)	V _{IN}	-10 +16	V
Current through input pin (DC)	I _{IN}	±2.0	mA
Current through status pin (DC)	I _{ST}	±5.0	
see internal circuit diagrams page 7			

Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	max	
Thermal resistance	chip - case:	R_{thJC}			7	K/W
junction - ambient (free air):		R_{thJA}			75	
SMI	D version, device on PCB ⁵⁾ :			39		

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Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins, e.g. with a 150 Ω resistor in the GND connection and a 15 k Ω resistor in series with the status pin. A resistor for the protection of the input is integrated.

 $^{^{3)}}$ $R_{\rm I}$ = internal resistance of the load dump test pulse generator

⁴⁾ V_{Load dump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

⁵⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.



Electrical Characteristics

Parameter and Conditions		Symbol	Values		Unit	
at $T_j = 25$ °C, $V_{bb} = 12$ V unless otherwise specified			min	typ	max	
Load Switching Capa	bilities and Characteristics					
On-state resistance (pi	n 3 to 5)					
$I_{L} = 1.8 \text{ A}$	<i>T</i> j=25 °C:	R_{ON}		160	200	mΩ
	<i>T</i> j=150 °C:			320	400	
Nominal load current, I $V_{ON} = 0.5 \text{ V}$, $T_C = 85 ^{\circ}$	I _{L(ISO)}	1.8	2.3		Α	
Output current (pin 5) while GND disconnected or GND pulled up, V_{bb} =30 V, V_{IN} = 0, see diagram page 8		I _{L(GNDhigh)}			10	mA
Turn-on time	IN \int to 90% V_{OUT} :	<i>t</i> on	80	200	400	μS
Turn-off time	IN \perp to 10% V_{OUT} :	$t_{ m off}$	80	200	400	
$R_{L} = 12 \Omega, T_{j} = -40+$						
Slew rate on		dV/dt _{on}	0.1		1	V/µs
10 to 30% V_{OUT} , $R_{L} =$						
Slew rate off 70 to 40% V_{OUT} , $R_L =$	12 Ω, <i>T</i> _j =-40+150°C	-d V/dt _{off}	0.1		1	V/μs

Operating Parameters

-						
Operating voltage ⁶⁾	<i>T</i> _j =-40+150°C:	$V_{\rm bb(on)}$	5.0		34	V
Undervoltage shutdown	<i>T</i> _j =-40+150°C:	V _{bb(under)}	3.5		5.0	V
Undervoltage restart	T _j =-40+25°C: T _j =+150°C:	V _{bb(u rst)}	-		5.0 7.0	V
Undervoltage restart of charge pump see diagram page 12 T_i =-40+150°C:		$V_{ m bb(ucp)}$	-	5.6	7.0	V
Undervoltage hysteresis $\Delta V_{\text{bb(under)}} = V_{\text{bb(urst)}} - V_{\text{bb(under)}}$		$\Delta V_{ m bb(under)}$	-	0.2		V
Overvoltage shutdown	<i>T</i> _j =-40+150°C:	$V_{ m bb(over)}$	34		43	V
Overvoltage restart	<i>T</i> _j =-40+150°C:	V _{bb(o rst)}	33			V
Overvoltage hysteresis	<i>T</i> _j =-40+150°C:	$\Delta V_{\rm bb(over)}$		0.5		V
Overvoltage protection ⁷⁾ I_{bb} =40 mA	<i>T</i> _j =-40+150°C:	$V_{\mathrm{bb}(AZ)}$	42	47		V
Standby current (pin 3)						
$V_{IN} = 0$	<i>T</i> _j =-40+25°C:	I _{bb(off)}		10	23	μΑ
	<i>T</i> _j = 150°C:			12	28	

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⁶⁾ At supply voltage increase up to V_{bb} = 5.6 V typ without charge pump, $V_{OUT} \approx V_{bb}$ - 2 V

 $^{^{7)}}$ See also $V_{\mbox{ON(CL)}}$ in table of protection functions and circuit diagram page 8.



Parameter and Conditions	Symbol		Values		Unit
at $T_j = 25$ °C, $V_{bb} = 12$ V unless otherwise specified		min	typ	max	
Leakage output current (included in Ibb(off)) Vin=0	I _{L(off)}			12	μА
Operating current (Pin 1) ⁸⁾ , V _{IN} =5 V, T _i =-40+150°C	<i>I</i> _{GND}		1.8	3.5	mA

Protection Functions9)

Initial peak short circuit current limit (pin 3 to 5)	I _{L(SCp)}				
$T_{j} = -40^{\circ}\text{C}:$ $T_{j} = 25^{\circ}\text{C}:$ $T_{j} = +150^{\circ}\text{C}:$		5.5 4.5 3	9.5 7.5 5	13 11 7	Α
Repetitive short circuit shutdown current limit	I _{L(SCr)}				
$T_{\rm j} = T_{\rm jt}$ (see timing diagrams, page 10)			4		Α
Output clamp (inductive load switch off) at $V_{\text{OUT}} = V_{\text{bb}} - V_{\text{ON(CL)}}$ $I_{\text{L}} = 40 \text{ mA}$:	V _{ON(CL)}	41	47	53	V
Thermal overload trip temperature	T_{jt}	150			°C
Thermal hysteresis	$\Delta T_{\rm jt}$		10		K
Reverse battery (pin 3 to 1) 10)	- V _{bb}			32	V

Diagnostic Characteristics

Open load detection current (on-condition)	<i>T</i> _j =-40 °C: <i>T</i> _j =25150°C:	I _{L (OL)}	10 10		200 150	mA
Open load detection voltage ¹¹⁾	(off-condition) T_j =-40150°C:	V _{OUT(OL)}	2	3	4	V
Internal output pull down (pin 5 to 1), $V_{OUT}=5 \text{ V}$, $T_j=-40$.	Ro	4	10	30	kΩ	

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⁸⁾ Add I_{ST} , if $I_{ST} > 0$, add I_{IN} , if $V_{IN} > 5.5 \text{ V}$

⁹⁾ Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

Requires 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 2 and circuit page 8).

¹¹⁾ External pull up resistor required for open load detection in off state.



Parameter and Conditions	Symbol		Values		Unit
at $T_j = 25$ °C, $V_{bb} = 12$ V unless otherwise specified		min	typ	max	
Input and Status Feedback ¹²⁾					
Input resistance see circuit page 7	Rı	2.5	3.5	6	kΩ
Input turn-on threshold voltage $\int T_j = -40+150$ °C:	$V_{IN(T+)}$	1.7		3.5	V
Input turn-off threshold voltage $\ \ \ \ T_j$ =-40+150°C:		1.5			V
Input threshold hysteresis	$\Delta V_{\text{IN(T)}}$		0.5		V
Off state input current (pin 2), $V_{IN} = 0.4 \text{ V}$, $T_j = -40+150$ °C	I _{IN(off)}	1		50	μΑ
On state input current (pin 2), $V_{IN} = 3.5 \text{ V}$, $T_j = -40+150$ °C	I _{IN(on)}	20	50	90	μΑ
Delay time for status with open load after switch off (see timing diagrams, page 11), $T_i = -40+150$ °C	t _{d(ST OL4)}	100	400	800	μS
Status invalid after positive input slope	$t_{ m d(ST)}$		250	600	μS
(open load)	, ,				
Status output (open drain)					
Zener limit voltage $T_j = -40 + 150$ °C, $I_{ST} = +1.6$ mA:	V _{ST(high)}	5.4	6.1		V
ST low voltage $T_{j} = -40 + 25$ °C, $I_{ST} = +1.6$ mA:	$V_{\rm ST(low)}$			0.4	
$T_{\rm j}$ = +150°C, $I_{\rm ST}$ = +1.6 mA:				0.6	

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 $^{^{\}rm 12)}\,$ If a ground resistor $R_{\rm GND}$ is used, add the voltage drop across this resistor.



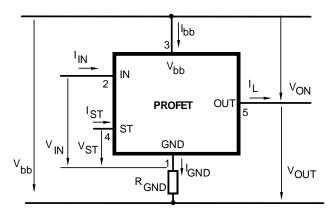
Truth Table

	Input-	Output	Status
	level	level	
Normal	L	L	Н
operation	Н	Н	Н
Open load	L	¹³)	H (L ¹⁴⁾)
	Н	Н	L
Short circuit	L	Н	∟ 15)
to V _{bb}	Н	Н	H (L ¹⁶⁾)
Overtem-	L	L	Н
perature	Н	L	L
Under-	L	L	Н
voltage	Н	L	Н
Overvoltage	L	L	Н
	Н	L	Н

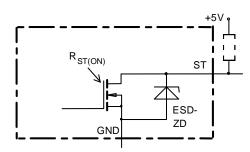
L = "Low" Level H = "High" Level X = don't care

Z = high impedance, potential depends on external circuit Status signal after the time delay shown in the diagrams (see fig 5. page 11...12)

Terms



Status output

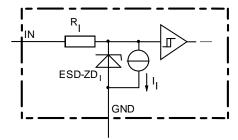


ESD-Zener diode: 6.1 V typ., max 5 mA;

 $R_{ST(ON)}$ < 380 Ω at 1.6 mA, ESD zener diodes are not to be used as voltage clamp at DC conditions.

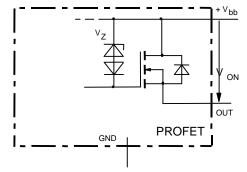
Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

Input circuit (ESD protection)



ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

Inductive and overvoltage output clamp



Von clamped to 47 V typ.

¹³⁾ Power Transistor off, high impedance

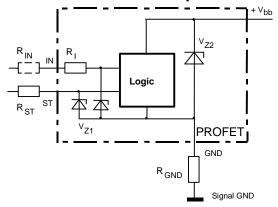
¹⁴⁾ with external resistor between pin 3 and pin 5

¹⁵⁾ An external short of output to V_{bb} , in the off state, causes an internal current from output to ground. If R_{GND} is used, an offset voltage at the GND and ST pins will occur and the V_{ST low} signal may be errorious.

¹⁶⁾ Low resistance to $V_{\rm bb}$ may be detected in ON-state by the no-load-detection



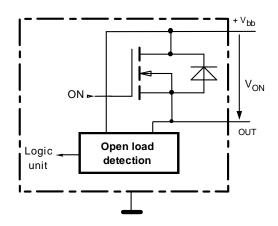
Overvolt. and reverse batt. protection



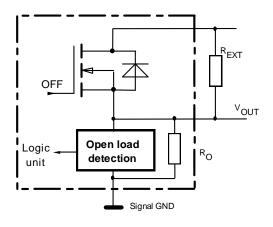
 V_{Z1} = 6.2 V typ., V_{Z2} = 47 V typ., R_{GND} = 150 Ω, R_{ST} = 15 kΩ, R_{I} = 3.5 kΩ typ.

Open-load detection

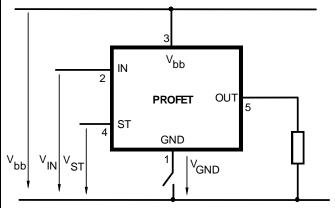
ON-state diagnostic condition: $V_{\rm ON}$ < $R_{\rm ON}$ * $I_{\rm L(OL)}$; IN high



OFF-state diagnostic condition: $V_{OUT} > 3 \text{ V typ.}$; IN low

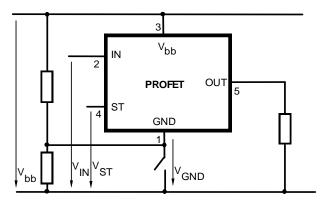


GND disconnect



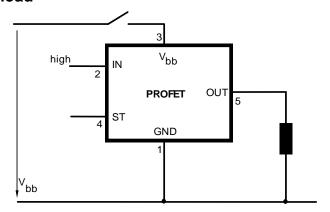
Any kind of load. In case of Input=high is $V_{OUT} \approx V_{IN} - V_{IN(T+)}$. Due to $V_{GND} > 0$, no $V_{ST} =$ low signal available.

GND disconnect with GND pull up



Any kind of load. If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off Due to $V_{GND} > 0$, no $V_{ST} =$ low signal available.

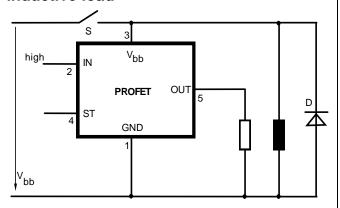
V_{bb} disconnect with energized inductive load



Normal load current can be handled by the PROFET itself.

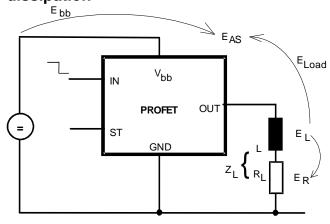


V_{bb} disconnect with charged external inductive load



If other external inductive loads L are connected to the PROFET, additional elements like D are necessary.

Inductive Load switch-off energy dissipation



Energy stored in load inductance:

$$E_L = \frac{1}{2} \cdot L \cdot I_L^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

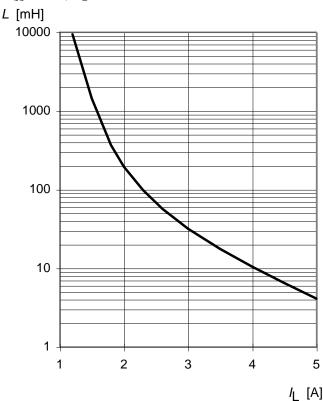
$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for $R_L > 0 \Omega$:

$$E_{AS} = \frac{I_{L} \cdot L}{2 \cdot R_{L}} \cdot \left(V_{bb} + |V_{OUT(CL)}| \right) \cdot ln \left(1 + \frac{I_{L} \cdot R_{L}}{|V_{OUT(CL)}|} \right)$$

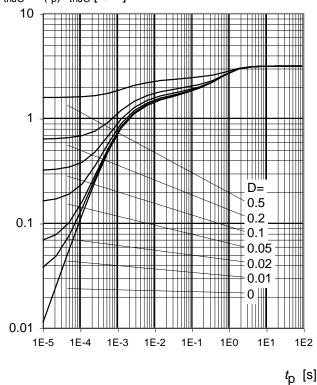
Maximum allowable load inductance for a single switch off

 $L = f(\bar{I_L}); T_{j,start} = 150$ °C, $T_C = 150$ °C const., $V_{bb} = 12 \text{ V}, R_L = 0 \Omega$



Transient thermal impedance chip case

 $Z_{thJC} = f(t_p)Z_{thJC} [K/W]$





Timing diagrams

Figure 1a: V_{bb} turn on:

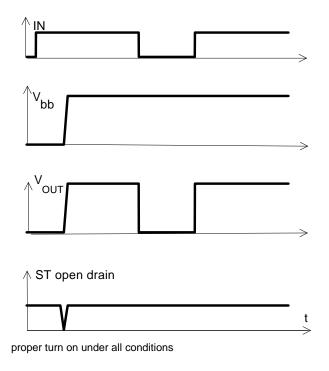


Figure 2a: Switching a lamp,

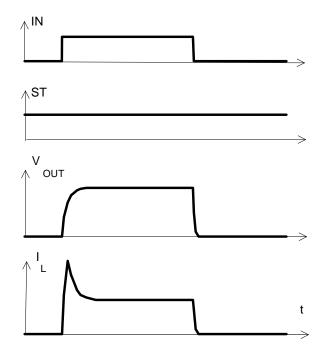
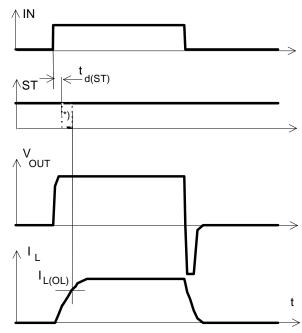
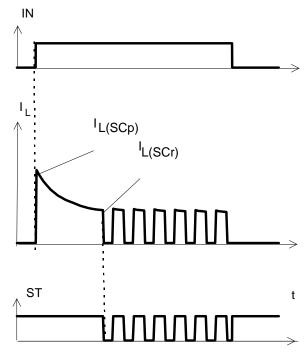


Figure 2b: Switching an inductive load



*) if the time constant of load is too large, open-load-status may occur

Figure 3a: Short circuit shut down by overtempertature, reset by cooling



Heating up may require several milliseconds, depending on external conditions



Figure 4a: Overtemperature: Reset if $T_i < T_{it}$

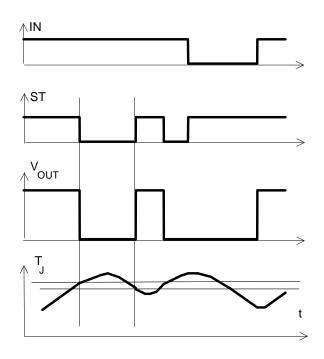
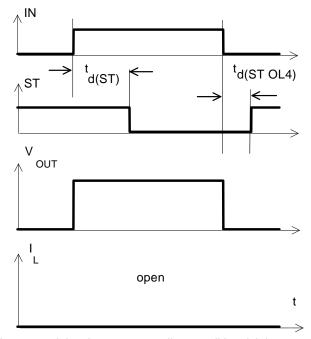


Figure 5a: Open load: detection in ON-state, turn on/off to open load



The status delay time $t_{\text{d(ST\ OL4)}}$ allows to ditinguish between the failure modes "open load" and "overtemperature".

Figure 5b: Open load: detection in ON-state, open load occurs in on-state

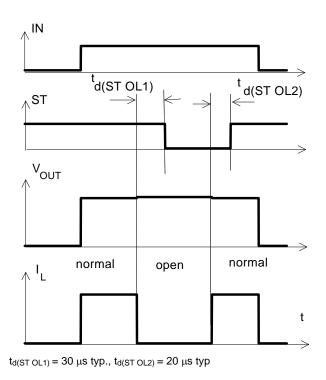


Figure 5c: Open load: detection in ON- and OFF-state (with R_{EXT}), turn on/off to open load

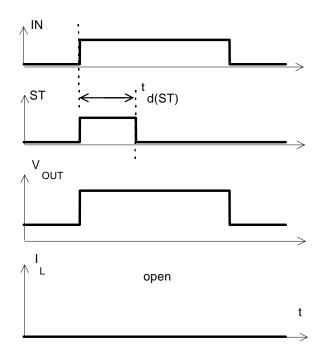




Figure 6a: Undervoltage:

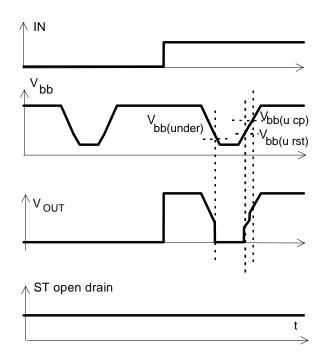


Figure 6b: Undervoltage restart of charge pump

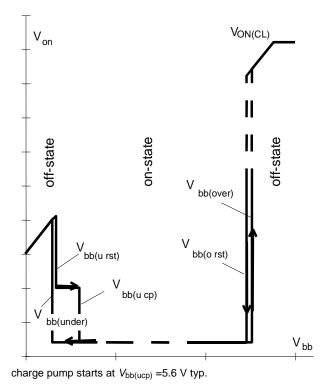
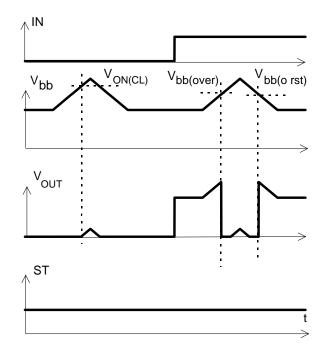


Figure 7a: Overvoltage:

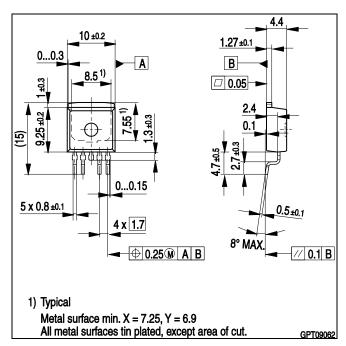




Package and Ordering Code

All dimensions in mm

PG-TO263-5-2	Ordering code
BTS409L1 E3062A	SP001104814



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